

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM6J507NU

#### 1. Applications

· Power Management Switches

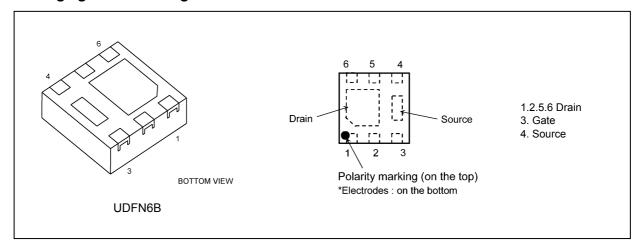
#### 2. Features

- (1) 4 V gate drive voltage.
- (2) Low drain-source on-resistance
  - $: R_{DS(ON)} = 20 \text{ m}\Omega \text{ (max) } (@V_{GS} = -10 \text{ V})$

 $R_{\rm DS(ON)} = 28 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.5 \ {\rm V})$ 

 $R_{DS(ON)} = 32 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.0 \text{ V})$ 

#### 3. Packaging and Pin Assignment





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	-30	V
Gate-source voltage				$V_{GSS}$	-25 / +20	
Drain current (DC)			(Note 1)	$I_D$	-10	Α
Drain current (pulsed)	·		(Note 1), (Note 2)	$I_{DP}$	-30	
Power dissipation			(Note 3)	$P_{D}$	1.25	W
Power dissipation	(t ≤	10 s)	(Note 3)	$P_{D}$	2.5	W
Channel temperature				$T_ch$	150	ç
Storage temperature			,	$T_{stg}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.
- Note 3: Device mounted on a FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	-	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	_		-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D$ = -250 $\mu$ A, $V_{GS}$ = 0 $V$	-30			V
Gate threshold voltage	(Note 1)	$V_{th}$	$V_{DS} = V_{GS}$ , $I_{D} = -250 \mu A$	-1.0	_	-2.2	
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -10 V	_	14	20	mΩ
			I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -4.5 V	_	19	28	
			I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -4.0 V	_	21	32	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	$V_{DS}$ = -10 V, $I_{D}$ = -2.0 A	_	14	_	S

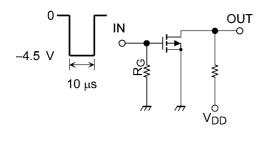
Note 1: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-250  $\mu$ A for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 2: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V,		1150	1	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		185		
Output capacitance	C <sub>oss</sub>			210		
Switching time (turn-on time)		$V_{DD}$ = -15 V, $I_{D}$ = -2.0 A $V_{GS}$ = 0 to -4.5 V, $R_{G}$ = 10 $\Omega$ ,	_	55	_	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%,V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> $<$ 5 ns, Common source, See Chapter 5.3.		170		

## 5.3. Switching Time Test Circuit



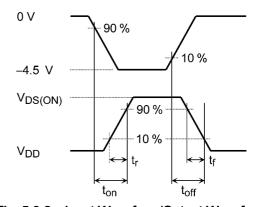


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -4.5 V,	_	13.6	20.4	nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -10 A	_	2.6	_	
Gate-drain charge	Q <sub>gd</sub>			5.8		

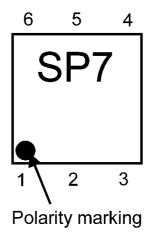


## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

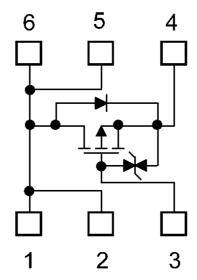
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 4 A, V <sub>GS</sub> = 0 V	_	0.78	1.0	V

Note 1: Pulse measurement.

## 6. Marking



## 7. Internal Equivalent Circuit



80

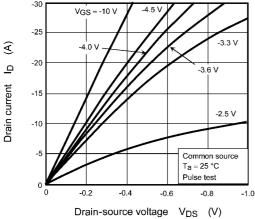
60

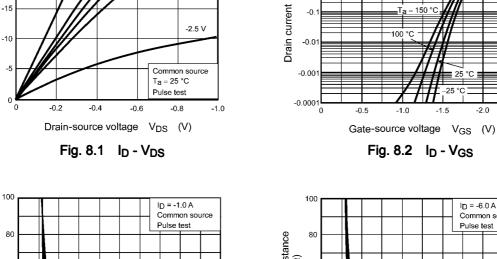
20

0

Drain-source on-resistance  $R_{DS(ON)} \ \ \, (m\Omega)$ 

#### 8. Characteristics Curves (Note)





100 °C

Gate-source voltage VGS (V) Fig. 8.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

150 °C

25 °C

-12

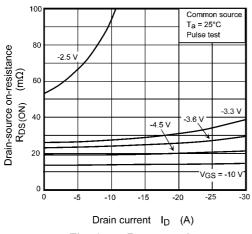


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

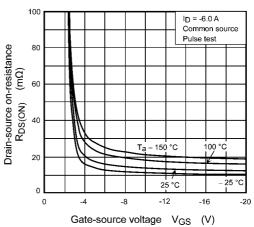


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

Common source

 $\overline{\mathfrak{C}}$ 

\_

-0.0

Fig. 8.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

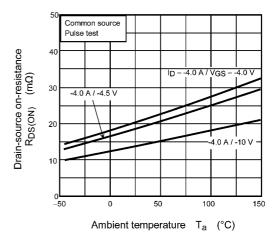


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

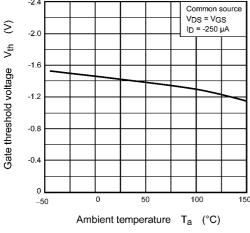


Fig. 8.7 V<sub>th</sub> - T<sub>a</sub>

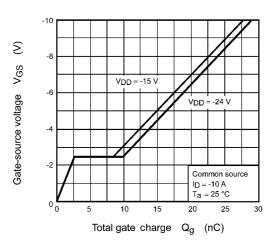


Fig. 8.9 Dynamic Input Characteristics

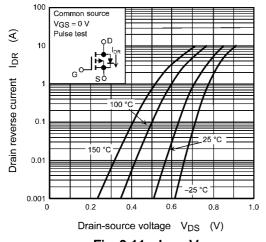


Fig. 8.11 I<sub>DR</sub> - V<sub>DS</sub>

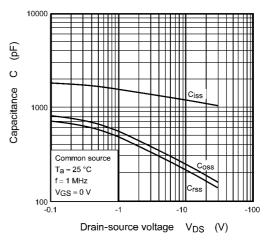


Fig. 8.8 C - V<sub>DS</sub>

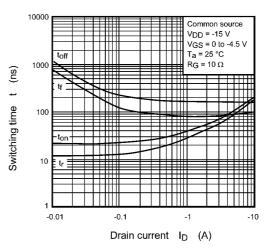


Fig. 8.10 t - I<sub>D</sub>

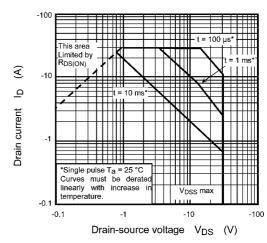
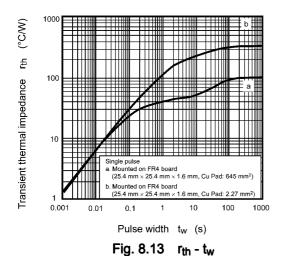


Fig. 8.12 Safe Operating Area



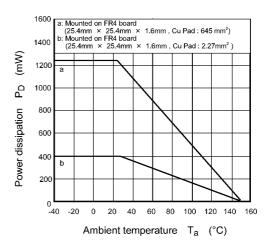


Fig. 8.14 PD - Ta

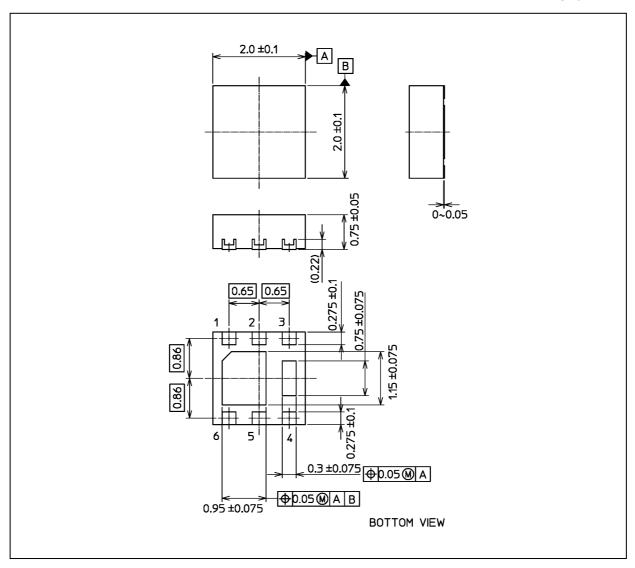
1.9.0...

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
TOSHIBA: 2-2AA1A	
Nickname: UDFN6B	



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